

FDC604P

P-Channel 1.8V Specified PowerTrench® MOSFET

General Description

This P-Channel 1.8V specified MOSFET uses Fairchild's low voltage PowerTrench process. It has been optimized for battery power management applications.

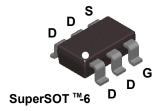
Applications

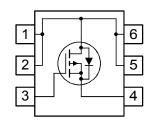
- · Battery management
- Load switch
- Battery protection

Features

• -5.5 A, -20 V. $\begin{aligned} R_{DS(ON)} &= 0.033 \ \Omega \ @\ V_{GS} = -4.5 \ V \\ R_{DS(ON)} &= 0.043 \ \Omega \ @\ V_{GS} = -2.5 \ V \\ R_{DS(ON)} &= 0.060 \ \Omega \ @\ V_{GS} = -1.8 \ V \end{aligned}$

- Fast switching speed.
- High performance trench technology for extremely low $R_{\mbox{\scriptsize DS(ON)}}$





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		±8	V
I _D	Drain Current - Continuous	(Note 1a)	-5.5	Α
	Pulsed		-20	
P _D	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T _J , T _{STG}	Operating and Storage Junction Temp	perature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Marking and Ordering Information

Device Marking	Device Marking Device		Tape width	Quantity	
.604	FDC604P	7"	8mm	3000 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			I	ı	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20			V
ΔBV _{DSS} ΔT, _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A,Referenced to 25°C		-12		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
I _{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -8 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	racteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.7	-1.5	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A,Referenced to 25°C		3		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$\begin{array}{cccc} V_{GS} = -4.5 \text{ V}, & I_D = -5.5 \text{ A} \\ V_{GS} = -2.5 \text{ V}, & I_D = -4.8 \text{ A} \\ V_{GS} = -1.8 \text{ V}, & I_D = -4.0 \text{ A} \end{array}$		0.024 0.030 0.042	0.033 0.043 0.060	Ω
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-20			Α
g FS	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -3.5 \text{ A}$		23		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$		1926		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		530		pF
C _{rss}	Reverse Transfer Capacitance	7		185		pF
Switchir	ng Characteristics (Note 2)			•		
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -10 \text{ V}, \qquad I_{D} = -1 \text{ A},$		13	23	ns
t _r	Turn-On Rise Time	$V_{DD} = -10 \text{ V}, \qquad I_{D} = -1 \text{ A},$ $V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		11	20	ns
$t_{d(off)}$	Turn-Off Delay Time	7		90	144	ns
t _f	Turn-Off Fall Time	7		45	72	ns
Qg	Total Gate Charge	$V_{DS} = -10 \text{ V}, I_{D} = -3.5 \text{ A},$		19	30	nC
Q _{gs}	Gate–Source Charge	V _{GS} = -4.5 V		4		nC
Q_{gd}	Gate-Drain Charge	7		7.5		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
I _s	Maximum Continuous Drain–Source				-1.3	Α
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -1.3 \text{ A} \text{(Note 2)}$		-0.7	-1.2	V

Notes

^{1.} $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a. 78°C/W when mounted on a 1in² pad of 2oz copper on FR-4 board.

b. 156°C/W when mounted on a minimum pad.

^{2.} Pulse Test: Pulse Width $\leq 300~\mu s,~Duty~Cycle \leq 2.0\%$

Typical Characteristics

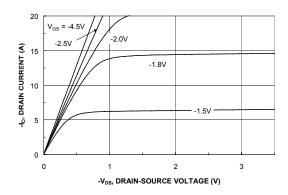


Figure 1. On-Region Characteristics.

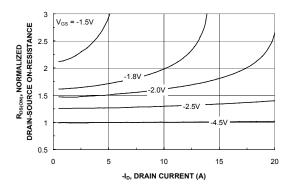


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

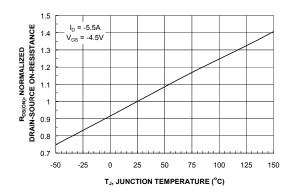


Figure 3. On-Resistance Variation withTemperature.

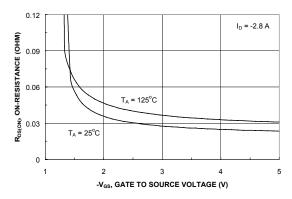


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

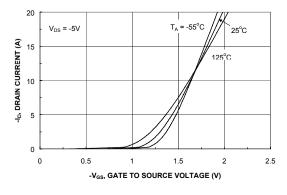


Figure 5. Transfer Characteristics.

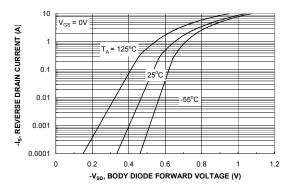
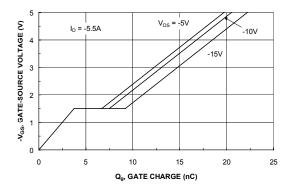


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

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Typical Characteristics



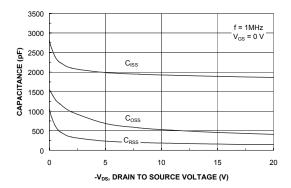


Figure 7. Gate Charge Characteristics.

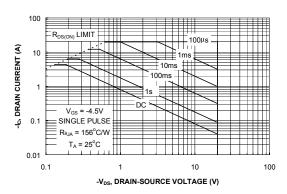


Figure 8. Capacitance Characteristics.

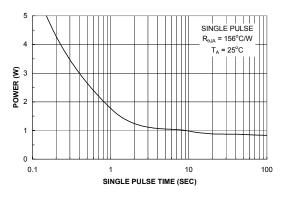


Figure 9. Maximum Safe Operating Area.



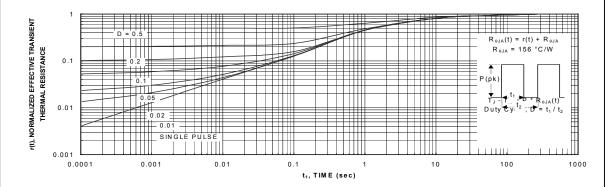
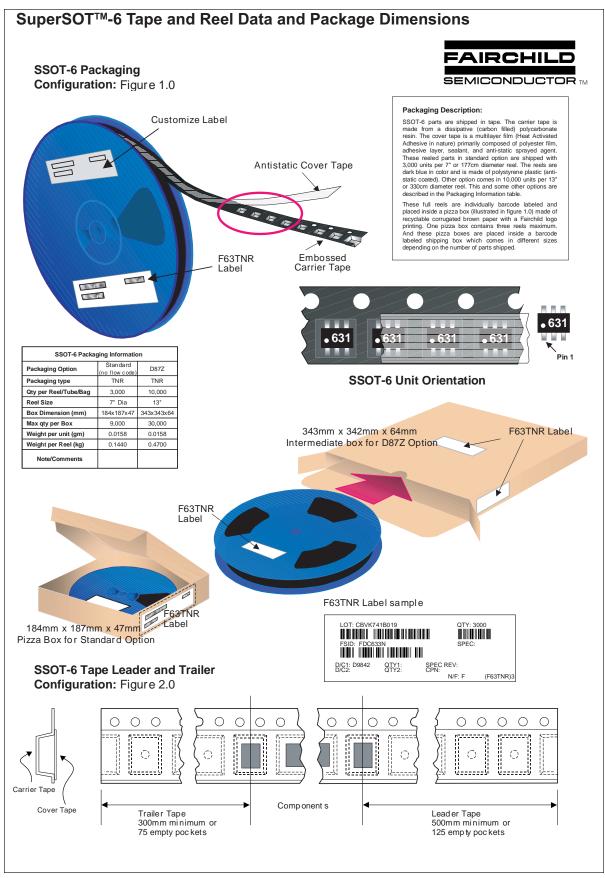
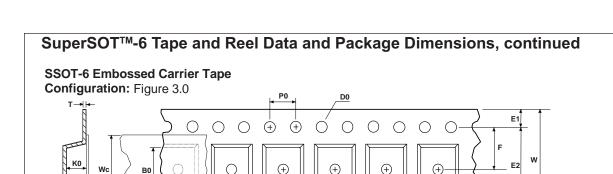


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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D1

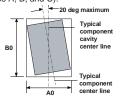
Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

A0

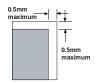


Sketch A (Side or Front Sectional View)
Component Rotation



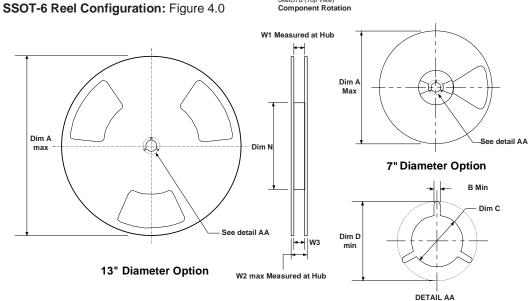
Sketch B (Top View)

Component Rotation



Sketch C (Top View)

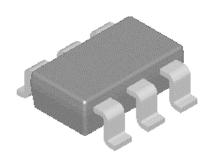
Component lateral movement

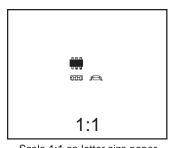


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SuperSOT™-6 Tape and Reel Data and Package Dimensions, continued

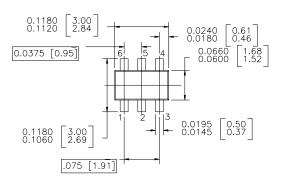
SuperSOT -6 (FS PKG Code 31, 33)

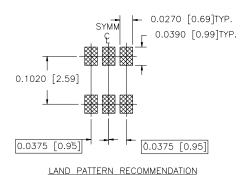




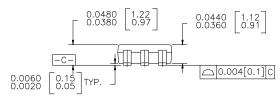
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

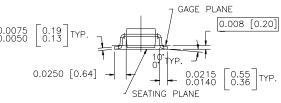
Part Weight per unit (gram): 0.0158





CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH: 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

 $2.0\ \mathsf{NO}\ \mathsf{JEDEC}\ \mathsf{REGISTRATION}\ \mathsf{AS}\ \mathsf{OF}\ \mathsf{JULY}\ 1996$

SUPER SOT 6 LEADS

September 1998, Rev. A

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Rev. B